



Future Normal in Semiconductor

2025-02-13(목), 15:50-17:20

좌장: 추후업데이트 예정

J. Nano-Science & Technology 분과

[TJ3-J] 2D Devices & Materials

<p>초청</p> <p>TJ3-J-1</p> <p>15:50-16:20</p>	<p>Process Emulation and Device Simulation of Gate-All-Around MoS₂ Nanosheet NMOSFET</p> <p>Sung-Min Hong and In Ki Kim</p> <p>School of Electrical Engineering and Computer Science, GIST</p>
<p>TJ3-J-2</p> <p>16:20-16:35</p>	<p>Investigation of Optimal Architecture with MoS₂ Channel Gate-All-Around FETs based on 0.7nm Process Node</p> <p>Junyeol Lee and Jongwook Jeon</p> <p>Department of Electrical and Computer Engineering, Sungkyunkwan University</p>
<p>TJ3-J-3</p> <p>16:35-16:50</p>	<p>Large-Area Implementation of Double-Gate Vertical Sidewall MoS₂ Field-Effect Transistors for Area-Efficient Integrated Circuit</p> <p>Jiwon Ma¹ and Jiwon Chang^{1,2}</p> <p>¹Department of Materials Science and Engineering, Yonsei University, ²Department of System Semiconductor Engineering, Yonsei University</p>
<p>TJ3-J-4</p> <p>16:50-17:05</p>	<p>Manipulating Thermal Conductivity of Monolayer MoS₂ by All-scale Hierarchical Phonon Scattering through Multi-scale Defects</p> <p>Mingyu Jang¹, Jeongin Yeo², Seonguk Yang², Sungkyu Kim³, Lina Yang⁴, and Joonki Suh^{1,2}</p> <p>¹Graduate School of Semiconductor Materials and Devices Engineering, UNIST, ²Department of Materials Science and Engineering, UNIST, ³Department of Nanotechnology and Advanced Materials Engineering, Sejong University, ⁴School of Aerospace Engineering, Beijing Institute of Technology</p>
<p>TJ3-J-5</p> <p>17:05-17:20</p>	<p>Explainable AI-Driven Insights into the Correlation of Raman Spectroscopy and Reduction Degree in Graphene Oxide</p> <p>Jaekak Yoo¹, Youngwoo Cho², Dong Hyeon Kim¹, Seung Mi Lee³, Jaegul Choo², and Mun Seok Jeong¹</p> <p>¹Hanyang University, ²KAIST, ³KRISS</p>